



睿晶科技股份有限公司
SILICON WORKS TECH CORPORATION

DSP SPEC

Growth method	Cz, MCz,
Diameter	200 mm, 150 mm
Crystal orientation	<100>, <111>
N type dopants	Antimony, Phosphorus, Arsenic
P type dopants	Boron
Resistivity	From 0.0008 to 100 Ohm-cm
Flatness	TTV<1um
	STIR<0.2um
	Warpage 200 mm: <20um, 150mm:<10um
Wafer thickness	200 mm: 400 μm to 1,000 μm
	150 mm: 375 μm to 1,000 μm